

S25FL129P

CS Q99628, Q99618, Q99745, Q99768

Qualification of: S25FL129P, 128-Mbit CMOS 3.0 Volt Flash Memory with 104-MHz SPI (Serial Peripheral Interface) Multi I/O Bus in SO3016, WNF008, FAB024 and FAC024.



Reliability Qualification Summary

CONFIDENTIAL

NOTICE: The material in this report is confidential. It is prepared to assist in the qualification of our product. It is declassified for the internal use of our customers only, and may be modified to meet the needs of specific customers. It also serves as a record of full qualification according to JESD47 and AEC-Q100 Grade 1 requirements.

Additionally, the package details (material set, assembly location, etc.) are specific to the qual vehicle used for the qualification. Alternate material sets and assembly locations may be qualified for the product. Production material can be assembled with any qualified material set and at any qualified assembly location. Tests are performed in accordance with AEC-Q100 and relevant JEDEC specifications.

Table of Contents

- I. Product Information
- II. Life Test Failure Rate Calculation
- III. Summary of Stress Test Results
- IV. Revision History

I.A. Product Information

Product Description: S25FL129P
 128-Mbit CMOS 3.0 Volt Flash Memory with 104-MHz SPI (Serial Peripheral Interface) Multi I/O Bus

Package: SO3016	Qualification: Q99628
Description: (10.3 x 10.3 x 2.65mm) 16 Lead, Small Outline Integrated Circuit (SOIC)	
Theta Ja: 38 °C/W	Psi Jt: 7.8 °C/W
Assembly Location: UTL Thailand	Molding Compound: RoHS Compliant Epoxy Resin
Substrate/Leadframe: Copper Leadframe	Die Attachment: Paste
Lead Finish: 100% Matte Sn Plating	Bond Wire: Gold
Comments:	

Est. Field Temperature: 55 °C	Life Test Temperature: 125 °C
Est. DC Field Current: 38 mA	Life Test Dynamic Current: 15 mA
Est. Field Voltage: 3.0 V	Life Test Voltage: 3.6 V
Est. Field Power Dissipation: 114 mWatts	Est. Stress Power Dissipation: 54 mWatts
Est. Field Tj: 59.3 °C	Est. Stress Tj: 127.0 °C

Die: 98U30A	Die Size: 3.49 x 6.23 mm
Process: CS129 (90nm)	Fab: Spansion Fab25
Type: MirrorBit	Density: 128M

I.B. Product Information

Product Description: S25FL129P
 128-Mbit CMOS 3.0 Volt Flash Memory with 104-MHz SPI (Serial Peripheral Interface) Multi I/O Bus

Package: WNF008	Qualification: Q99618
Description: (6.0 x 8.0 x 0.75mm) 8 Contact, Small Outline No Lead Package (WSON)	
Theta Ja: 18 °C/W	Psi Jt: 8.8 °C/W
Assembly Location: UTL Thailand	Molding Compound: RoHS Compliant Epoxy Resin
Substrate/Leadframe: Copper Leadframe	Die Attachment: Film
Lead Finish: 100% Matte Sn Plating	Bond Wire: Gold
Comments:	

Est. Field Temperature: 55 °C	Life Test Temperature: 150 °C
Est. DC Field Current: 26 mA	Life Test Dynamic Current: 12 mA
Est. Field Voltage: 3.0 V	Life Test Voltage: 3.6 V
Est. Field Power Dissipation: 78 mWatts	Est. Stress Power Dissipation: 43.2 mWatts
Est. Field Tj: 56.3 °C	Est. Stress Tj: 150.7 °C

Die: 98U30A	Die Size: 3.49 x 6.23 mm
Process: CS129 (90nm)	Fab: Spansion Fab25
Type: MirrorBit	Density: 128M

I.C. Product Information

Product Description: S25FL129P
 128-Mbit CMOS 3.0 Volt Flash Memory with 104-MHz SPI (Serial Peripheral Interface) Multi I/O Bus

Package: FAB024	Qualification: Q99745
Description: (8 x 6 x 1.2mm) 24 Ball, Fine Pitch Ball Grid Array Package (FBGA)	
Theta Ja: 39 °C/W	Psi Jt: 11 °C/W
Assembly Location: Spansion Thailand	Molding Compound: RoHS Compliant Epoxy Resin
Substrate/Leadframe: BT Resin Substrate	Die Attachment: Paste
Lead Finish: 96.5Sn3.0Ag0.5Cu Spheres	Bond Wire: Gold
Comments:	

Est. Field Temperature: 55 °C	Life Test Temperature: 150 °C
Est. DC Field Current: 26 mA	Life Test Dynamic Current: 12 mA
Est. Field Voltage: 3.0 V	Life Test Voltage: 3.6 V
Est. Field Power Dissipation: 78 mWatts	Est. Stress Power Dissipation: 43.2 mWatts
Est. Field Tj: 58.0 °C	Est. Stress Tj: 151.6 °C

Die: 98U30A	Die Size: 3.49 x 6.23 mm
Process: CS129 (90nm)	Fab: Spansion Fab25
Type: MirrorBit	Density: 128M

I.D. Product Information

Product Description: S25FL129P
 128-Mbit CMOS 3.0 Volt Flash Memory with 104-MHz SPI (Serial Peripheral Interface) Multi I/O Bus

Package: FAC024	Qualification: Q99768
Description: (8 x 6 x 1.2mm) 24 Ball, Fine Pitch Ball Grid Array Package (FBGA)	
Theta Ja: 39 °C/W	Psi Jt: 11 °C/W
Assembly Location: Spansion Thailand	Molding Compound: RoHS Compliant Epoxy Resin
Substrate/Leadframe: BT Resin Substrate	Die Attachment: Paste
Lead Finish: 96.5Sn3.0Ag0.5Cu Spheres	Bond Wire: Gold
Comments:	

Est. Field Temperature: 55 °C	Life Test Temperature: 150 °C
Est. DC Field Current: 26 mA	Life Test Dynamic Current: 12 mA
Est. Field Voltage: 3.0 V	Life Test Voltage: 3.6 V
Est. Field Power Dissipation: 78 mWatts	Est. Stress Power Dissipation: 43.2 mWatts
Est. Field Tj: 58.0 °C	Est. Stress Tj: 151.6 °C

Die: 98U30A	Die Size: 3.49 x 6.23 mm
Process: CS129 (90nm)	Fab: Spansion Fab25
Type: MirrorBit	Density: 128M

II. CS129/AL Life Test Failure Rate Calculation

HTOL Stress Temperature - 150 °C

Failure Mechanism	Read Points / Test Results				Modeling Parameters @ 55°C					Avg. Failure Rate FITS @ 55°C, 60% Conf.	
	24 hrs	168 hrs	1000 hrs	2000 hrs	Ea eV	TAF	VAF	OAF	MTTF (yrs)	Early Life	Inherent Life
PLASTIC											
Sample Size	9884	11035	1660	150							
Zero fails, Process ave. Ea	0 *	0	0	0	0.66	145	1	145		22	2
Totals	0	0	0	0					57078	22	2

* Contributes to early life FITS

Data Retention Bake - 150 °C

Reliability Stress	Number of Rejects	Sample Size	Failure Rate %	Failure Mechanism
500 hrs	0	3426	0.00	No Failures
1000 hrs	0	3650	0.00	No Failures

III. Summary of Stress Test Results

Stress Test	Stress Condition	Package Type	Sample Size	Num. of Lots	Num. of Fails	Failure Rate %	Comments
Data From Qualification Q99628, Q99618, Q99745, Q99768:							
HTOL (EL)	(3.6V, 125°C)	SO3016 ¹	200	1	0	0.00	168 hours
ESD CDM	N/A	SO3016 ¹	15	1	Passed	1.0kV	
	N/A	WNF008 ²	15	1	Passed	1.0kV	
	N/A	FAB024 ³	15	1	Passed	1.0kV	
ESD HBM	(100pF, 1500 Ohms)	SO3016 ¹	60	1	Passed	2.0kV	
Latch Up	(125°C, +/- 100mA)	SO3016 ¹	6	1	Passed		
Endurance (10k)	(105°C, 3.6V)	SO3016 ¹	64	1	0	0.00	10k cycles
	(25°C, 3.6V)	SO3016 ¹	64	1	0	0.00	10k cycles
	(-40°C, 3.6V)	SO3016 ¹	64	1	0	0.00	10k cycles
	(90°C, 3.6V)	SO3016 ¹	64	1	0	0.00	10k cycles
Preconditioning	(PC9/260°C, +0°C/-5°C)	SO3016 ¹	77	1	Passed	Jedec L3 / Jeita Rank E	
	(PC1/260°C, +0°C/-5°C)	WNF008 ²	77	1	Passed	Jedec L3 / Jeita Rank E	
	(PC1/260°C, +0°C/-5°C)	FAB024 ³	77	1	Passed	Jedec L3 / Jeita Rank E	
	(PC1/260°C, +0°C/-5°C)	FAC024 ⁴	77	1	Passed	Jedec L3 / Jeita Rank E	
Precon+Temp Cycle	(PC1/260°C, -40°C/150°C)	WNF008 ²	77	1	0	0.00	1000 cycles

Generic Reference Data:

ESD CDM	N/A	SO3016 ⁹	15	1	Passed 1.0kV		
Preconditioning	(PC1/260°C, +0°C/-5°C)	SO3016 ⁵	691	3	Passed Jedec L3 / Jeita Rank E		
	(PC1/260°C, +0°C/-5°C)	WNF008 ⁶	229	1	Passed Jedec L3 / Jeita Rank E		
	(PC1/260°C, +0°C/-5°C)	LAA064 ⁷	229	1	Passed Jedec L3 / Jeita Rank E		
	(PC1/260°C, +0°C/-5°C)	FAA064 ⁸	77	1	Passed Jedec L3 / Jeita Rank E		
	(PC9/260°C, +0°C/-5°C)	SO3016 ⁹	77	1	Passed Jedec L3 / Jeita Rank E		
Precon+Temp Cycle	(PC1/260°C, -40°C/150°C)	SO3016 ⁵	229	3	0	0.00	1000 cycles
	(PC1/260°C, -40°C/150°C)	WNF008 ⁶	77	1	0	0.00	1000 cycles
	(PC1/260°C, -40°C/150°C)	LAA064 ⁷	75	1	0	0.00	1000 cycles
	(PC1/260°C, -40°C/150°C)	FAA064 ⁸	77	1	0	0.00	1000 cycles
	(PC9/260°C, -40°C/150°C)	SO3016 ⁹	77	1	0	0.00	500 cycles
Precon+HAST	(PC1/260°C, Biased, 130°C/85% RH)	SO3016 ⁵	231	3	0	0.00	96 hours
	(PC1/260°C, Biased, 130°C/85% RH)	WNF008 ⁶	77	1	0	0.00	96 hours
	(PC1/260°C, Biased, 110°C/85% RH)	LAA064 ⁷	77	1	0	0.00	264 hours
Precon+Steam Pressure	(PC1/260°C, 121°C/100%RH/15PSIG)	WNF008 ⁶	75	1	0	0.00	168 hours
	(PC1/260°C, 121°C/100%RH/15PSIG)	LAA064 ⁷	77	1	0	0.00	168 hours
Precon+uHAST	(PC1/260°C, Unbiased, 130°C/85% RH)	SO3016 ⁵	231	3	0	0.00	96 hours

- Notes / Justification:**
- 1) Results from Qual Q99628, S25FL129P, 128M CS129 (90nm) MirrorBit in 16 Lead SOIC (10.3 x 10.3 x 2.65mm)
 - 2) Results from Qual Q99618, S25FL129P, 128M CS129 (90nm) MirrorBit in 8 Contact WSON (6 x 8 x 0.75mm)
 - 3) Results from Qual Q99745, S25FL129P, 128M CS129 (90nm) MirrorBit in 24 Ball FBGA (8 x 6 x 1.2mm)
 - 4) Results from Qual Q99768, S25FL129P, 128M CS129 (90nm) MirrorBit in 24 Ball FBGA (8 x 6 x 1.2mm)
 - 5) Results from Qual Q99050a, S25FL064A in 16 Lead SOIC (10.3 x 10.3 x 2.65mm) - Same SO3016 package and Assembly Location
 - 6) Results from Qual 81301, S25FL128P in 8 Contact WSON (6 x 8 x 0.75mm) - Same WSON package and Assembly Location
 - 7) Results from Qual 81292, S29GL01GP in 64 Ball fFBGA (13 x 11 x 1.4mm) - Same material Set and Similar fFBGA Package
 - 8) Results from Qual 80731, S29GL256N in 64 Ball FBGA (13 x 10 x 1.2mm) - Same material Set and Similar fFBGA Package
 - 9) Results from Qual Q99617, S25FL129P in 16 Lead SOIC (10.3 x 10.3 x 2.65mm) - Same SO3016 Package and Assembly Location

Preconditioning Flows: PC1 (Exceeds JEDEC L3 and JEITA Rank E): Bake 125°C, 24hr => Soak @ 30°C/70%RH, 216hr => 3x Reflow
 PC9 (Accelerated JEDEC L3 / JEITA Rank E): Bake 125°C, 24hr => Soak @ 60°C/70%RH, 72hr => 3x Reflow

IV. Revision History

Section	Description
Revision A - 8/13/2012	
	Initial Release.

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